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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/905,090	07/12/2001	Jerome D. Lescot	SNTCP001X2C1	4622
7590 07/06/2004			EXAMINER	
MANI ADELI, ESQ. STATTLER, JOHANSEN & ADELI LLP			JONES, HUGH M	
P.O. BOX 51860			ART UNIT	PAPER NUMBER
PALO ALTO, CA 94303-0728			2128	

DATE MAILED: 07/06/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)			
Office Action Summary		09/905,090	LESCOT ET AL.			
		Examiner	Art Unit			
		Hugh Jones	2128			
Period fo	The MAILING DATE of this communication a or Reply	ppears on the cover sheet with the c	orrespondence address			
THE - Exte after - If the - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR REF MAILING DATE OF THIS COMMUNICATION nsions of time may be available under the provisions of 37 CFR SIX (6) MONTHS from the mailing date of this communication. e period for reply specified above is less than thirty (30) days, a representation of the provision of t	N. 1.136(a). In no event, however, may a reply be timely within the statutory minimum of thirty (30) days of will apply and will expire SIX (6) MONTHS from the cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. D (35 U.S.C. § 133).			
Status						
1)[🖂	Responsive to communication(s) filed on 12	July 2001.				
2a)[This action is FINAL . 2b)⊠ Th	nis action is non-final.	$\widehat{\chi}$			
3)□) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.					
Disposit	ion of Claims		•			
 4) Claim(s) 2-20 is/are pending in the application. 4a) Of the above claim(s) is/are withdrawn from consideration. 5) Claim(s) is/are allowed. 6) Claim(s) 2-20 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/or election requirement. 						
Applicati	ion Papers					
9) The specification is objected to by the Examiner.						
10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner.						
	Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).					
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d). 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.						
Priority ι	under 35 U.S.C. § 119					
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received.						
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Attachmen	• •	-				
2) Notice	te of References Cited (PTO-892) te of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449 or PTO/SB/0 ter No(s)/Mail Date 8/24/2001.	4) Interview Summary Paper No(s)/Mail Da 8)				

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DETAILED ACTION

1. Claims 2-20 of U. S. Application 09/905,090, filed July 1, 2001, which is a continuation of U. S. Application 09/536,206, filed 3/29/2000 are pending.

Double Patenting

- 2. The nonstatutory double patenting rejection is based on a judicially created doctrine grounded in public policy (a policy reflected in the statute) so as to prevent the unjustified or improper timewise extension of the "right to exclude" granted by a patent and to prevent possible harassment by multiple assignees. See *In re Goodman*, 11 F.3d 1046, 29 USPQ2d 2010 (Fed. Cir. 1993); *In re Longi*, 759 F.2d 887, 225 USPQ 645 (Fed. Cir. 1985); *In re Van Ornum*, 686 F.2d 937, 214 USPQ 761 (CCPA 1982); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970);and, *In re Thorington*, 418 F.2d 528, 163 USPQ 644 (CCPA 1969).
- 3. A timely filed terminal disclaimer in compliance with 37 CFR 1.321(c) may be used to overcome an actual or provisional rejection based on a nonstatutory double patenting ground provided the conflicting application or patent is shown to be commonly owned with this application. See 37 CFR 1.130(b).
- 4. Effective January 1, 1994, a registered attorney or agent of record may sign a terminal disclaimer. A terminal disclaimer signed by the assignee must fully comply with 37 CFR 3.73(b).
- 5. Claims 2-20 are rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims 1-11 of U.S. Patent No. 6,291,324. Although the conflicting claims are not identical, they are not patentably distinct from each other.
- 6. The instant application claims the medium and apparatus for carrying out the invention, but does not claim the method.
- 7. It would have been obvious to one of ordinary skill in the art at the time of the invention to use the apparatus and medium as claimed in the instant application to implement the method as claimed in the issued patent.

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Allowable Subject Matter

8. Claims 2-20 are allowable over the prior art of record and will be allowed when the double patenting rejections are traversed.

9. The following is a statement of reasons for the indication of allowable subject matter: The physics of semiconductor profiles and doping is well known. However, the prior art of record does not disclose or suggest the "access key", in the context of the claimed invention.

Conclusion

- 10. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.
- Shin et al. disclose: a new MOS transistor structural approach (hot-carrier-induced MOSFET) capable of substantially suppressing adverse hot-carrier effects, while maintaining the other desired performance and manufacturability characteristics of deep-submicrometer MOSFETs (L gate ⩽ 0.35 μm) is described. This structure is unique in having a lower doped N region located behind (or above) a very shallow, steeply profiled source/drain junction. In contrast, LDD types of MOSFETs have an N region with a more graded **doping profile** immediately adjacent to the channel region. The **simulated** characteristics of the HCS MOSFET structure indicate approximately one order of magnitude less substrate current in comparison to an LDD type of MOSFET whose structure and doping parameters are optimized for combined performance, reliability, and manufacturability. In terms of combined performance, reliability, and manufacturability, the HCS MOSFET should permit MOSFET devices to be more successfully scaled at deep-submicrometer dimensions.
- 11. Any inquiry concerning this communication or earlier communications from the examiner should be:

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directed to:

Dr. Hugh Jones telephone number (703) 305-0023, Monday-Thursday 0830 to 0700 ET, *or* the examiner's supervisor, Kevin Teska, telephone number (703) 305-9704.

Any inquiry of a general nature or relating to the status of this application should be directed to the Group receptionist, telephone number (703) 305-3900.

mailed to:

Commissioner of Patents and Trademarks

Washington, D.C. 20231

or faxed to:

(703) 308-9051 (for formal communications intended for entry)

or (703) 308-1396 (for informal or draft communications, please label PROPOSED or DRAFT).

Dr. Hugh Jones

Primary Patent Examiner

June 25, 2004

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